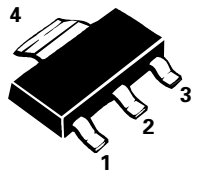
SOT223 PNP SILICON PLANAR DARLINGTON TRANSISTORS

ISSUE 5– MARCH 2001 ✪

FZTA64

PARTMARKING DETAILS: FZTA64

COMPLIMENTARY TYPE: FZTA14



SOT223

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-10	V
Peak Pulse Current	I_{CM}	-800	mA
Continuous Collector Current	I_C	-500	mA
Peak Base Current	I_{BM}	-200	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	2	W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

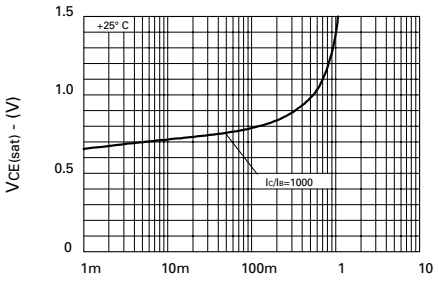
PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-30		V	I_C=-10μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30		V	I_C=-10mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-10		V	I_E=-10μA, I_C=0
Collector Cut-Off Current	I_{CBO}		-100	nA	V_{CB}=-30V, I_E=0
Emitter Cut-Off Current	I_{EBO}		-100	nA	V_{EB}=-10V, I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-1.5	V	I_C=-100mA, I_B=-0.1mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-2.0	V	I_C=-100mA, I_B=-0.1mA*
Static Forward Current Transfer Ratio	h_{FE}	10K 20K			IC=-10mA, V_{CE}=-5V I_C=-100mA, V_{CE}=-5V*
Transition Frequency	f_T	125		MHz	I_C=-50mA, V_{CE}=-5V f=20MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

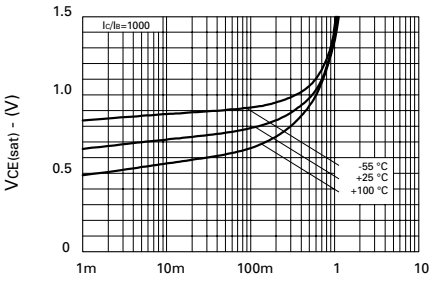
ZETEX

FZTA64

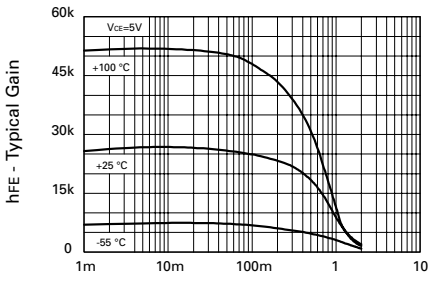
TYPICAL CHARACTERISTICS



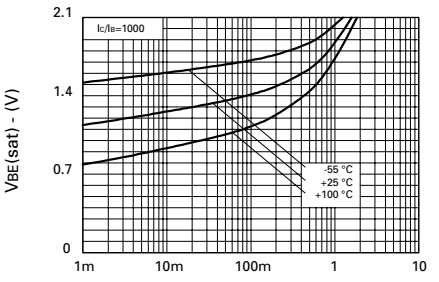
VCE(sat) v IC



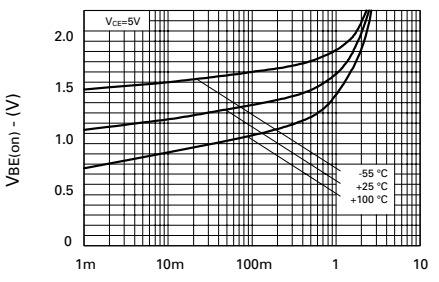
VCE(sat) v IC



hFE v IC



VBE(sat) v IC



VBE(on) v IC